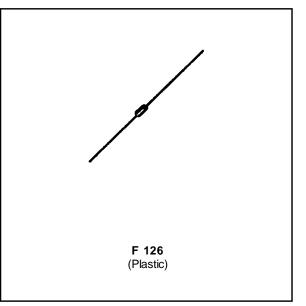


STPR310 STPR320

ULTRA FAST RECOVERY RECTIFIER DIODES

- SUITED FOR SMPS
- LOW LOSSES
- LOW FORWARD AND REVERSE RECOVERY TIME
- HIGH SURGE CURRENT CAPABILITY
- HIGH AVALANCHE ENERGY CAPABILITY



DESCRIPTION

Low cost single chip rectifier suited for switchmode power supply and high frequency DC to DC converters.

Packaged in F 126, this device is intended for use in low voltage, high frequency inverters, free wheeling and polarity protection applications.

ABSOLUTE RATINGS (limiting values)

Symbol	Parameter	Value	Unit	
lF(AV)	Average Forward Current	$TI = 60^{\circ}C$ $\delta = 0.5$	3	А
IFSM	Surge Non Repetitive Forward Current	Tp = 10 ms Sinusoidal	30	А
Tstg Tj	Storage and Junction Temperature Range		- 65 to + 150 - 65 to + 150	°C

Symbol	Parameter	STPR		Unit
		310	320	
VRRM	Repetitive Peak Reverse Voltage	100	200	V

THERMAL RESISTANCE

Symbol	Parameter	Value	Unit
Rth (j-l)*	Junction-leads	25	°C/W

* ou infinite heatsink with L = 5mm lead length.

STPR310/STPR320

ELECTRICAL CHARACTERISTICS

STATIC CHARACTERISTICS

Symbol	Tests Conditions			Тур.	Max.	Unit
I _R *	Tj = 25°C	V _R = V _{RRM}			10	μΑ
	Tj = 100°C				0.5	mA
VF **	Tj = 125°C	IF = 3 A			0.99	V
	Tj = 125°C	IF = 6 A			1.20	
	Tj = 25°C	IF = 6 A			1.25	

Pulse test : * tp = 5 ms, duty cycle < 2 % ** tp = 380 μ s, duty cycle < 2%

RECOVERY CHARACTERISTICS

Symbol	Tests Conditions			Min.	Тур.	Max.	Unit	
trr	Tj = 25°C	IF = 0.5 A	I _R = 1A	Irr = 0.25 A			30	ns
tfr	Tj = 25°C	IF = 1 A	tr = 10 ns	V _{FR} = 1.1 x V _F		20		ns
VFP	Tj = 25°C	I _F = 1 A	tr = 10 ns			3		V

To evaluate the conduction losses use the following equation : P = 0.78 x IF(AV) + 0.070 IF²(RMS)



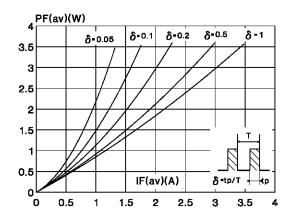


Fig.1 : Average forward power dissipation versus average forward current.

Fig.2 : Peak current versus form factor.

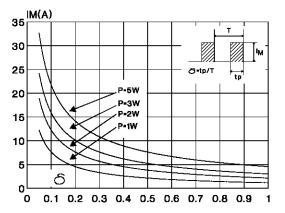


Fig.3 : Average current versus ambient temperature. (duty cycle : 0.5)

circuit board e (Cu) = $35\mu m$, S (cu) = $12mm^2$ L(LEADS)= 20mm

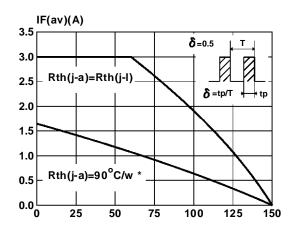
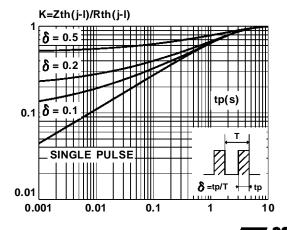


Fig.5 : Relative variation of thermal transient impedance junction to case versus pulse duration.



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Fig.4 : Non repetitive surge peak forward current versus overload duration. (Maximum values)

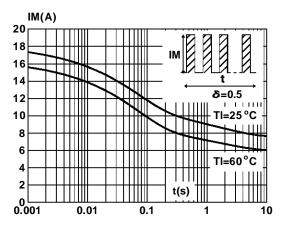
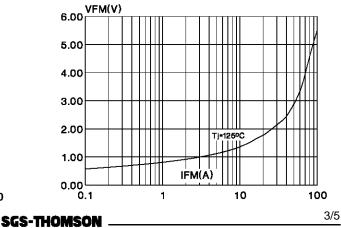


Fig.6 : Forward voltage drop versus forward current. (Maximum values)



STPR310/STPR320

Fig.7: Junction capacitance versus reverse voltage applied. (Typical values)

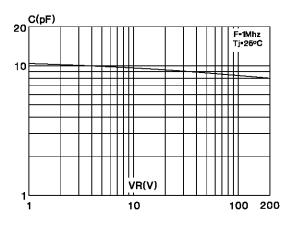


Fig.9 : Peak reverse current versus dIF/dt.

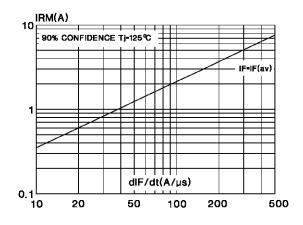


Fig.8 : Recovery charge versus dIF/dt.

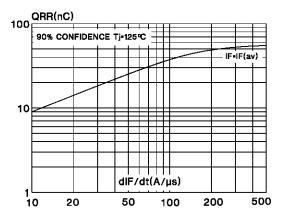
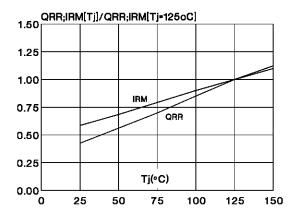
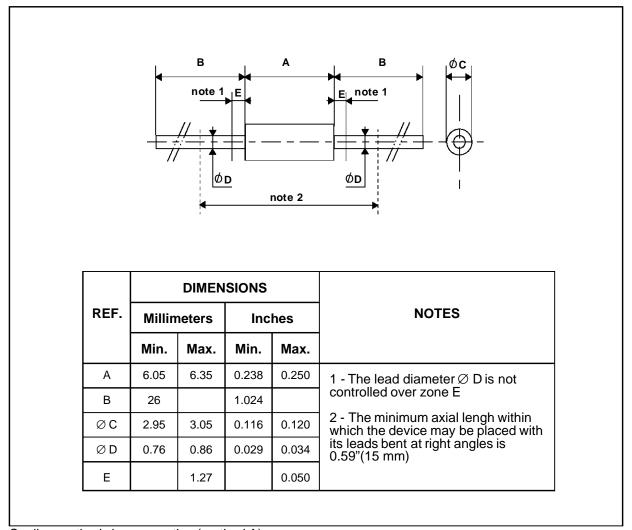


Fig.10 : Dynamic parameters versus junction temperature.





PACKAGE MECHANICAL DATA F126



Cooling method : by convention (method A) Marking : Clear, ring at cathode end Weight : 0.4 g

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